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	Application No.	Applicant(s)	
Notice of Allowability	09/815,670	YOSHIDA ET AL.	
	Examiner	Art Unit	•
	Quyen P. Leung	2828	
The MAILING DATE of this communication of All claims being allowable, PROSECUTION ON THE MERITA herewith (or previously mailed), a Notice of Allowance (PTOL NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1	S IS (OR REMAINS) CLOSED in 85) or other appropriate commur IT RIGHTS. This application is su	this application. If not included nication will be mailed in due co	urse. <b>THIS</b>
1. $\square$ This communication is responsive to $\underline{10/25/2004}$ .			
2. The allowed claim(s) is/are 1,5,9,13 and 30.			
3. The drawings filed on 23 March 2001 are accepted by	the Examiner.		
<ul> <li>4.  Acknowledgment is made of a claim for foreign priori</li> <li>a)  All b)  Some* c)  None of the:</li> <li>1.  Certified copies of the priority documents</li> <li>2.  Certified copies of the priority documents</li> <li>3.  Copies of the certified copies of the priorit International Bureau (PCT Rule 17.2(a)).</li> <li>* Certified copies not received:</li> </ul>	have been received. have been received in Application	No	n from the
	TE" of this common in the common to		
Applicant has THREE MONTHS FROM THE "MAILING DA noted below. Failure to timely comply will result in ABANDO THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	TE of this communication to file a ONMENT of this application.	a reply complying with the requi	rements
5. A SUBSTITUTE OATH OR DECLARATION must be s INFORMAL PATENT APPLICATION (PTO-152) which	ubmitted. Note the attached EXAI gives reason(s) why the oath or o	MINER'S AMENDMENT or NOT declaration is deficient.	TICE OF
6. CORRECTED DRAWINGS ( as "replacement sheets")	must be submitted.		
(a)  including changes required by the Notice of Drafts		(PTO-948) attached	
1)  hereto or 2)  to Paper No./Mail Date	<del></del>		
<ul><li>(b) ☐ including changes required by the attached Exami Paper No./Mail Date</li></ul>	iner's Amendment / Comment or i	n the Office action of	
Identifying indicia such as the application number (see 37 C each sheet. Replacement sheet(s) should be labeled as such	FR 1.84(c)) should be written on the	drawings in the front (not the ba	ack) of
<ol> <li>DEPOSIT OF and/or INFORMATION about the d attached Examiner's comment regarding REQUIREME</li> </ol>	eposit of BIOLOGICAL MATE	RIAL must be submitted. Not	e the
Attachment(s) 1. ☐ Notice of References Cited (PTO-892)	5. ☐ Notice of Info	rmal Patent Application (PTO-1	(52)
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-9-		• • • • • • • • • • • • • • • • • • • •	(32)
3. ☐ Information Disclosure Statements (PTO-1449 or PTO/S	Paper No./M	lail Date mendment/Comment	
<ol> <li>Examiner's Comment Regarding Requirement for Depo</li> </ol>	sit 8. 🛭 Examiner's S	tatement of Reasons for Allowa	ince
of Biological Material	9. ☐ Other		
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Application/Control Number: 09/815,670

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## **EXAMINER'S AMENDMENT**

1. In response to applicant's amendment after notice of appeal filed 10/25/2004, claims 25-29 have been canceled. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

- In claim 1 line 10 "strip" has been changed to –stripe—for proper antecedent basis.
- In claim 9 line 10 "strip" has been changed to –stripe—for proper antecedent basis.
- In claim 30 line 7 "strip" has been changed to –stripe—for proper antecedent basis.
- 2. The following is an examiner's statement of reasons for allowance:

Claims 1 and 5 are allowed mainly because the cited prior art do not teach or fairly suggest a ridge stripe Group III-nitride semiconductor laser comprising a current injection width between 1 micron and 3 microns, inclusively, a <u>non-zero</u> combined thickness (0.2 microns or less) of AlGaN layer(s), which are located between the current blocking layer and the active layer and have an AlN molar concentration between 0.3 and 1, inclusively.

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Claims 9, 13 and 30 are allowed mainly because the cited prior art do not teach or fairly suggest a ridge stripe Group III-nitride semiconductor laser comprising <u>a non-zero</u> combined thickness (0.2 microns or less) of AlGaN layer(s), which are located between the current blocking layer and the active layer and have an AlN molar concentration between 0.15 and 0.30, inclusively.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Quyen P. Leung whose telephone number is (571)272-1943. The examiner can normally be reached on 8-4:30, M-F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Minsun Harvey can be reached on (571)272-1835. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

> Quyen P. Leung **Primary Examiner** Art Unit 2828

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